

General Features

- Advanced Trench Technology
- Lead free product is acquired
- Provide Excellent RDS(ON) and Low Gate Charge

Product Summary



V _{DSS}	100	V
RDS(ON)-Typ	24	mΩ
lo	34	A

Application

- Load Switch
- PWM Application
- Power management





Absolute Maximum Ratings (Tc=25°C unless otherwise specified)

Symbol	Parameter		Max.	Units
V _{DSS}	Drain-Source Voltage		100	V
V _{GSS}	Gate-Source Voltage		±20	V
Ι _D	Continuous Drain Current	T _C = 25℃	34	A
		T _C = 100℃	20	A
I _{DM}	Pulsed Drain Current note1		120	Α
EAS	Single Pulsed Avalanche Energy note2		110	mJ
PD	Power Dissipation	T _C = 25℃	63	W
R _{θJC}	Thermal Resistance, Junction to Case		2.5	°C/W
TJ, TSTG	Operating and Storage Temperature Range		-55 to +175	°C



Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter Test Condition		Min.	Тур.	Max.	Units	
Off Characteristic							
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250µA	100	-	-	V	
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =100V, V _{GS} =0V,	-	-	1.0	μA	
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} =±20V	-	-	±100	nA	
On Characteristics							
V _{GS(th)}	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu A$	1.0	1.5	2.5	V	
	Static Drain-Source on-Resistance	V _{GS} =10V, I _D =20A	-	24	32	mΩ	
RDS(on)	note2	V _{GS} =4.5V, I _D =10A	-	26	36	mΩ	
Dynamic C	haracteristics						
C _{iss}	Input Capacitance		-	1500	-	pF	
Coss	Output Capacitance	$V_{DS}=25V, V_{GS}=0V,$	-	380	-	pF	
Crss	Reverse Transfer Capacitance		-	252	-	pF	
Qg	Total Gate Charge		-	23	-	nC	
Q _{gs}	Gate-Source Charge	$V_{DS}=30V, I_{D}=15A,$	-	5	-	nC	
Q _{gd}	Gate-Drain("Miller") Charge	V _{GS} =10V	-	4	-	nC	
Switching Characteristics							
t _{d(on)}	Turn-on Delay Time		-	12.6	-	ns	
tr	Turn-on Rise Time	V _{DS} =30V, I _D =15A,	-	6	-	ns	
t _{d(off)}	Turn-off Delay Time	R _G =1.8Ω, V _{GS} =10V	-	22	-	ns	
t _f	Turn-off Fall Time		-	5.3	-	ns	
Drain-Sou	rce Diode Characteristics and Maxim	um Ratings					
Is	Maximum Continuous Drain to Source Diode Forward Current		-	-	30	А	
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current			-	120	А	
V _{SD}	Drain to Source Diode Forward	V _{GS} =0V, I _S =30A	-	-	1.2	V	
trr	Rody Diode Reverse Recovery Time			71		ne	
ui	Body Diode Reverse Recovery Time	IE=15A dl/dt=100A/us	-		-	115	
Qrr	Charge	μ - τοπ,αι/αι- τουπ/μs	-	145	-	nC	

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition : T_J=25 $^\circ \!\! \mathbb{C}$,V_DD=50V,V_G=10V,L=0.5mH,Rg=25\Omega

3. Pulse Test: Pulse Width≤300µs, Duty Cycle≤0.5%



Test Circuit



Figure1:Gate Charge Test Circuit & Waveform



Figure 2: Resistive Switching Test Circuit & Waveforms



Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms







Typical Electrical and Thermal Characteristics (Curves)

ID (A)

















Figure 7: Normalized Breakdown Voltage vs. Junction Temperature







Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



Junction Temperature



Figure 10: Maximum Continuous Drain Current vs. Case Temperature



Ordering and Marking Information

Ordering Device No.	Marking	Package	Packing	Quantity
JMD100N34KQ-R	100N34	TO-252	Tape&Reel	2500





TO-252 PACKAGE IN FORMATION







Recommended Land Pattern



Symbol	Dimensions in Millimeters		Dimensions in Inches		
	Min	Max	Min	Max	
А	2.25	2.65	0.089	0.104	
A1	0.00	0.15	0.000	0.006	
A2	2.20	2.40	0.087	0.094	
b	0.50	0.70	0.020	0.028	
b1	0.70	0.90	0.028	0.035	
С	0.46	0.66	0.018	0.026	
c1	0.46	0.66	0.018	0.026	
D	6.30	6.70	0.248	0.264	
D1	5.20	5.40	0.205	0.213	
E	5.30	5.70	0.209	0.224	
E1	1.40	1.60	0.055	0.063	
Н	9.40	9.90	0.370	0.390	
е	2.30 TYP		0.09 TYP		
L	1.40	1.77	0.055	0.070	
L1	0.50	0.70	0.020	0.028	
θ	0°	8°	0°	8°	



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